

Saroj P Dash

List of Publications by Year in descending order

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218677

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43
docs citations

43
times ranked

4316
citing authors

#	ARTICLE	IF	CITATIONS
1	Challenges and opportunities in 2D heterostructures for electronic and optoelectronic devices. IScience, 2022, 25, 103942.	4.1	38
2	Microwave Synthesized 2D Gold and Its 2D-2D Hybrids. Journal of Physical Chemistry Letters, 2022, 13, 6487-6495.	4.6	14
3	Salt-assisted growth of monolayer MoS ₂ for high-performance hysteresis-free field-effect transistor. Journal of Applied Physics, 2021, 129, .	2.5	19
4	Disorder is not always bad for charge-to-spin conversion in WTe ₂ . Matter, 2021, 4, 1440-1441.	10.0	1
5	All-electrical creation and control of spin-galvanic signal in graphene and molybdenum ditelluride heterostructures at room temperature. Communications Physics, 2021, 4, .	5.3	20
6	Electrical Control of Hybrid Monolayer Tungsten Disulfideâ€™ Plasmonic Nanoantenna Lightâ€™ Matter States at Cryogenic and Room Temperatures. ACS Nano, 2020, 14, 1196-1206.	14.6	41
7	Magnetic proximity in a van der Waals heterostructure of magnetic insulator and graphene. 2D Materials, 2020, 7, 015026.	4.4	80
8	Unconventional Chargeâ€™ Spin Conversion in Weylâ€™ Semimetal WTe ₂ . Advanced Materials, 2020, 32, e2000818.	21.0	83
9	Two-dimensional spintronic circuit architectures on large scale graphene. Carbon, 2020, 161, 892-899.	10.3	32
10	Gate-tunable spin-galvanic effect in graphene-topological insulator van der Waals heterostructures at room temperature. Nature Communications, 2020, 11, 3657.	12.8	76
11	Observation of surface dominated topological transport in strained semimetallic ErPdBi thin films. Applied Physics Letters, 2020, 117, 132406.	3.3	3
12	Robust Spin Interconnect with Isotropic Spin Dynamics in Chemical Vapor Deposited Graphene Layers and Boundaries. ACS Nano, 2020, 14, 15864-15873.	14.6	12
13	Electrically Controlled Spin Injection from Giant Rashba Spinâ€™ Orbit Conductor BiTeBr. Nano Letters, 2020, 20, 4782-4791.	9.1	27
14	Charge-spin conversion signal in WTe ₂ van der Waals hybrid devices with a geometrical design. Applied Physics Letters, 2020, 117, .	3.3	9
15	Observation of charge to spin conversion in Weyl semimetal WTe_2 at room temperature. Physical Review Research, 2020, 2, .		
16	Charge-spin conversion in layered semimetal Ta_2Te_5 and spin injection in van der Waals heterostructures. Physical Review Research, 2020, 2, .		
17	Electrically controlled spin-switch and evolution of Hanle spin precession in graphene. 2D Materials, 2019, 6, 035042.	4.4	12
18	Manipulation of exciton and trion quasiparticles in monolayer WS ₂ via charge transfer. Applied Physics Letters, 2019, 115, .	3.3	14

#	ARTICLE	IF	CITATIONS
19	Origin and evolution of surface spin current in topological insulators. Physical Review B, 2018, 97, .	3.2	33
20	1D ferromagnetic edge contacts to 2D graphene/h-BN heterostructures. 2D Materials, 2018, 5, 014001.	4.4	26
21	Surface dominated magnetotransport in Bi ₂ Te _{2.15} Se 0.85 topological insulator. Journal of Applied Physics, 2018, 124, 214302.	2.5	1
22	Tailoring emergent spin phenomena in Dirac material heterostructures. Science Advances, 2018, 4, eaat9349.	10.3	65
23	Spin-Polarized Tunneling through Chemical Vapor Deposited Multilayer Molybdenum Disulfide. ACS Nano, 2017, 11, 6389-6395.	14.6	53
24	Gate-tunable Hall sensors on large area CVD graphene protected by h-BN with 1D edge contacts. Journal of Applied Physics, 2017, 122, .	2.5	20
25	Hall sensors batch-fabricated on all-CVD h-BN/graphene/h-BN heterostructures. Scientific Reports, 2017, 7, 15231.	3.3	33
26	Electrical gate control of spin current in van der Waals heterostructures at room temperature. Nature Communications, 2017, 8, 16093.	12.8	224
27	Inversion of Spin Signal and Spin Filtering in Ferromagnet Hexagonal Boron Nitride-Graphene van der Waals Heterostructures. Scientific Reports, 2016, 6, 21168.	3.3	79
28	Room Temperature Electrical Detection of Spin Polarized Currents in Topological Insulators. Nano Letters, 2015, 15, 7976-7981.	9.1	141
29	Low Schottky Barrier Black Phosphorus Field-Effect Devices with Ferromagnetic Tunnel Contacts. Small, 2015, 11, 2209-2216.	10.0	111
30	Tunnel magnetoresistance with atomically thin two-dimensional hexagonal boron nitride barriers. Nano Research, 2015, 8, 1357-1364.	10.4	87
31	Graphene spintronics: the European Flagship perspective. 2D Materials, 2015, 2, 030202.	4.4	243
32	Long distance spin communication in chemical vapour deposited graphene. Nature Communications, 2015, 6, 6766.	12.8	202
33	Effect of high-k dielectric and ionic liquid gate on nanolayer black-phosphorus field effect transistors. Applied Physics Letters, 2015, 107, .	3.3	18
34	Spin transport and precession in graphene measured by nonlocal and three-terminal methods. Applied Physics Letters, 2014, 104, .	3.3	36
35	Spintronics with graphene-hexagonal boron nitride van der Waals heterostructures. Applied Physics Letters, 2014, 105, 212405.	3.3	43
36	High-Performance Molybdenum Disulfide Field-Effect Transistors with Spin Tunnel Contacts. ACS Nano, 2014, 8, 476-482.	14.6	187

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37	Surface Energy Engineering for Tunable Wettability through Controlled Synthesis of MoS ₂ . Nano Letters, 2014, 14, 4314-4321.	9.1	258
38	Enhanced Tunnel Spin Injection into Graphene using Chemical Vapor Deposited Hexagonal Boron Nitride. Scientific Reports, 2014, 4, 6146.	3.3	142
39	Efficient Spin Injection into Silicon and the Role of the Schottky Barrier. Scientific Reports, 2013, 3, 3196.	3.3	69
40	Thermal creation of electron spin polarization in n-type silicon. Applied Physics Letters, 2013, 103, .	3.3	10
41	Initial stages of growth of iron on silicon for spin injection through Schottky barrier. Physica Status Solidi (B): Basic Research, 2011, 248, 2300-2304.	1.5	2
42	Oscillatory spin-polarized tunnelling from silicon quantum wells controlled by electric field. Nature Materials, 2010, 9, 133-138.	27.5	40
43	Electrical creation of spin polarization in silicon at room temperature. Nature, 2009, 462, 491-494.	27.8	565